

BLV57

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

BLV57 is Designed for use as push-pull amplifier, primarily in linear UHF TV transmitting Applications.

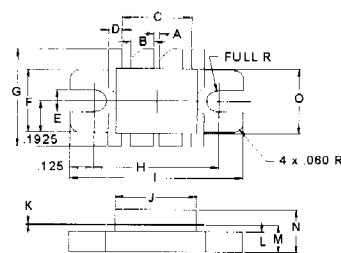
FEATURES:

- Input Matching Network
- Common emitter
- **OmniGold™** Metalization System with eutectic die bonding

MAXIMUM RATINGS

I_C	2.0 A
V_{CESM}	50 V
V_{CE}	27 V
P_{DISS}	77 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	2.27 $^\circ C/W$

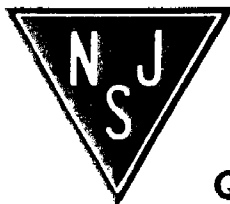
PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches/mm	MAXIMUM inches/mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 25\text{ mA}$	27			V
BV_{CES}	$I_C = 10\text{ mA}$	50			V
BV_{EBO}	$I_E = 5.0\text{ mA}$	3.5			V
I_{CES}	$V_E = 27\text{ V}$			10	mA
h_{FE}	$V_{CE} = 25\text{ V}$ $I_C = 850\text{ mA}$	15			---
f_T	$V_{CB} = 25\text{ V}$ $I_E = 1.7\text{ A}$ $V_{CB} = 25\text{ V}$ $I_E = 850\text{ mA}$		2.5 2.5		GHz
P_G IMD_1	$V_{CE} = 25\text{ V}$ $I_C = 850\text{ mA}$ $f = 860\text{ MHz}$ $P_{OUT} = 6.0\text{ W}$	8.0 -60			dB dBc



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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